

Description

Features

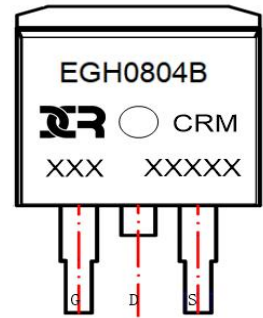
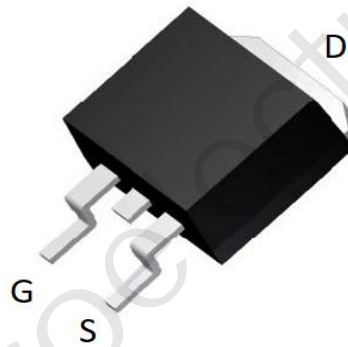
- 80V, 117A
 $R_{DS(ON)}$ Typ = 4.5mΩ @ $V_{GS} = 10V$
 Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_d s TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMEGH0804B	CRMEGH0804B	TO-263-3L	TAPING	13"	800	4000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units	
V _{DS}	Drain-to-Source Voltage	80	V	
V _{GS}	Gate-to-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	117	A
		T _C = 100°C	70.2	A
I _{DM}	Pulsed Drain Current ⁽¹⁾	468	A	
E _{AS}	Single Pulsed Avalanche Energy ⁽²⁾	281	mJ	
P _D	Power Dissipation	T _C = 25°C	139	W
R _{θJC}	Thermal Resistance, Junction to Case	0.9	°C/W	
T _J , T _{STG}	Junction & Storage Temperature Range	-55 to 150	°C	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	80	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 20A	-	4.5	5.9	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 40V, f = 1MHz	-	3468	-	pF
C _{oss}	Output Capacitance		-	660	-	pF
C _{rss}	Reverse Transfer Capacitance		-	13	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 40V, I _D = 55A	-	48	-	nC
Q _{gs}	Gate Source Charge		-	15	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	14	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 40V I _D = 55A, R _{GEN} = 1.6Ω	-	16	-	ns
t _r	Turn-On Rise Time		-	15	-	ns
t _{d(off)}	Turn-Off DelayTime		-	40	-	ns
t _f	Turn-Off Fall Time		-	12	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	117	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	468	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 30A, di/dt = 100A/us	-	40	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	165	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 40\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 33.5\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

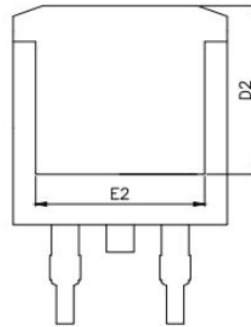
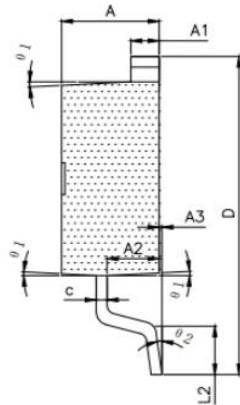
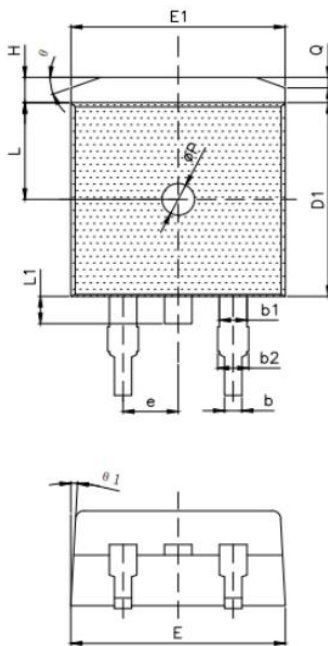


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-263-3L)




SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.20	1.30	1.40
A2	2.30	2.40	2.50
A3	0.03	0.13	0.23
b	0.70	0.80	0.90
b1	1.21	1.27	1.40
b2	1.25	1.35	1.45
c	0.40	0.50	0.60
D	14.80	15.10	15.40
D1	9.10	9.20	9.30
D2	8.00	—	—
E	9.70	9.90	10.20
E1	9.68	9.88	10.08
E2	7.80	—	—
e	2.54 (BSC)		
H	1.00	1.20	1.40
L	4.30	4.60	4.90
L1	1.10	1.30	1.50
L2	2.10	2.30	2.50
φP	1.40	1.50	1.60
Q	0.50 (REF)		
θ	16°	20°	24°
θ1	1°	3°	5°
θ2	0°	—	9°

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For sales information, please send an email to: sales@crm-semi.com